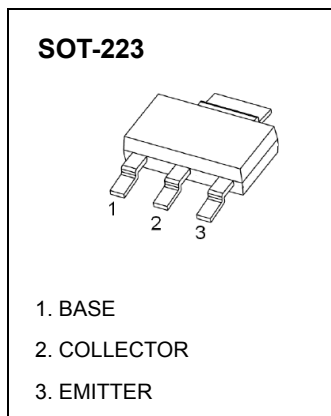


SOT-223 Plastic-Encapsulate Transistors

B772 TRANSISTOR (PNP)

FEATURES

- Power Dissipation:1.25W
- Low Collector-emitter Saturation Voltage



MAXIMUM RATINGS(T_a=25 °C unless otherwise not)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	-40	V
V _{CEO}	Collector-Emitter Voltage	-30	V
V _{EBO}	Emitter-Base Voltage	-6	V
I _C	Collector Current -Continuous	-3	A
P _C	Collector Dissipation	1.25	W
R _{θJA}	Thermal Resistance from Junction to Ambient	100	°C/W
T _J	Junction Temperature	150	
T _{stg}	Storage Temperature	-55~+150	

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-100μA, I _E =0	-40			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-10mA, I _B =0	-30			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-100 μA, I _C =0	-6			V
Collector cut-off current	I _{CBO}	V _{CB} =-40 V, I _E =0			-1	μA
Collector cut-off current	I _{CEO}	V _{CE} =-30 V, I _B =0			-10	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-6V, I _C =0			-1	μA
DC current gain	h _{FE (1)}	V _{CE} =2V, I _C =-1A	60		400	
	h _{FE (2)}	V _{CE} =-2V, I _C =-100mA	32			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-2A, I _B =-0.2A			-0.5	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =-2A, I _B =-0.2A			-1.5	V
Transition frequency	f _T	V _{CE} =-5V, I _C =-0.1A f=10MHz	50			MHz

CLASSIFICATION of h_{FE(1)}

Rank	R	O	Y	GR
Range	60-120	100-200	160-320	200-400

